MOSFETs Silicon N-Channel MOS (DTMOSIV-H)

# **TK22A65X**

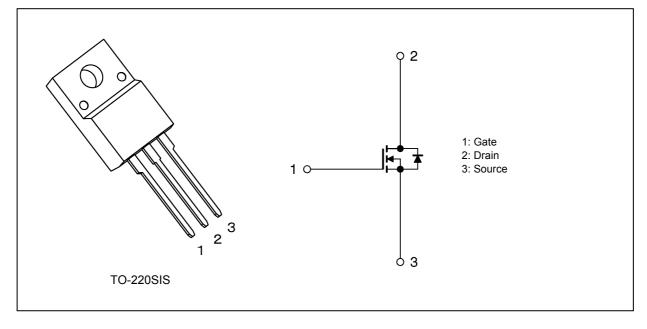
#### 1. Applications

• Switching Voltage Regulators

#### 2. Features

- (1) Low drain-source on-resistance:  $R_{DS(ON)} = 0.12 \Omega$  (typ.) by using Super Junction Structure: DTMOS
- (2) Easy to control Gate switching
- (3) Enhancement mode:  $V_{th}$  = 2.5 to 3.5 V (V\_{DS} = 10 V,  $I_{D}$  = 1.1 mA)

#### 3. Packaging and Internal Circuit



#### 4. Absolute Maximum Ratings (Note) (T<sub>a</sub> = 25 °C unless otherwise specified)

Characteristics		Sym	bol	Rating	Unit
Drain-source voltage		V <sub>DS</sub>	SS	650	V
Gate-source voltage		V <sub>G</sub>	SS	±30	
Drain current (DC)	(Note 1	) I <sub>D</sub>	)	22	A
Drain current (pulsed)	(Note 1	) I <sub>DI</sub>	5	88	
Power dissipation (	T <sub>c</sub> = 25 °C)	P	)	45	W
Single-pulse avalanche energy	(Note 2	) E <sub>A</sub>	S	361	mJ
Single-pulse avalanche current		I <sub>AS</sub>	3	5.5	A
Reverse drain current (DC)	(Note 1	) I <sub>Df</sub>	٦	22	A
Reverse drain current (pulsed)	(Note 1	) I <sub>DR</sub>	P	88	A
Channel temperature	·	Tc	h	150	°C
Storage temperature		T <sub>st</sub>	g	-55 to 150	
Isolation voltage (RMS)	(t = 1.0 s)	V <sub>ISO(I</sub>	RMS)	2000	V
Mounting torque		ТО		0.6	N·m

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

#### 5. Thermal Characteristics

Characteristics	Symbol	Max	Unit
Channel-to-case thermal resistance	R <sub>th(ch-c)</sub>	2.78	°C/W
Channel-to-ambient thermal resistance		62.5	

Note 1: Ensure that the channel temperature does not exceed 150 °C.

Note 2: V<sub>DD</sub> = 90 V, T<sub>ch</sub> = 25 °C (initial), L = 21.15 mH, R<sub>G</sub> = 25  $\Omega$ , I<sub>AS</sub> = 5.5 A

Note: This transistor is sensitive to electrostatic discharge and should be handled with care.

#### 6. Electrical Characteristics

#### 6.1. Static Characteristics (T<sub>a</sub> = 25 °C unless otherwise specified)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Gate leakage current	I <sub>GSS</sub>	$V_{GS}$ = ±30 V, $V_{DS}$ = 0 V	_	_	±1	μA
Drain cut-off current	I <sub>DSS</sub>	$V_{DS}$ = 650 V, $V_{GS}$ = 0 V	_	_	10	
Drain-source breakdown voltage	V <sub>(BR)DSS</sub>	I <sub>D</sub> = 10 mA, V <sub>GS</sub> = 0 V	650	_	—	V
Gate threshold voltage	V <sub>th</sub>	V <sub>DS</sub> = 10 V, I <sub>D</sub> = 1.1 mA	2.5	_	3.5	
Drain-source on-resistance	R <sub>DS(ON)</sub>	V <sub>GS</sub> = 10 V, I <sub>D</sub> = 11 A	_	0.12	0.15	Ω

#### 6.2. Dynamic Characteristics (Ta = 25 °C unless otherwise specified)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Input capacitance	C <sub>iss</sub>	V <sub>DS</sub> = 300 V, V <sub>GS</sub> = 0 V, f = 100 kHz	_	2400	_	pF
Reverse transfer capacitance	C <sub>rss</sub>		_	6	_	
Output capacitance	C <sub>oss</sub>		_	60	_	
Effective output capacitance	C <sub>o(er)</sub>	$V_{DS}$ = 0 to 400 V, $V_{GS}$ = 0 V	_	82	_	
Gate resistance	r <sub>g</sub>	V <sub>DS</sub> = OPEN , f = 1 MHz	_	1.7	_	Ω
Switching time (rise time)	t <sub>r</sub>	See Figure 6.2.1	_	15	_	ns
Switching time (turn-on time)	t <sub>on</sub>		_	45	_	
Switching time (fall time)	t <sub>f</sub>		_	5	_	
Switching time (turn-off time)	t <sub>off</sub>	]	_	90	_	1
MOSFET dv/dt ruggedness	dv/dt	V <sub>DS</sub> = 0 to 400 V, I <sub>D</sub> = 11 A	50	_	_	V/ns

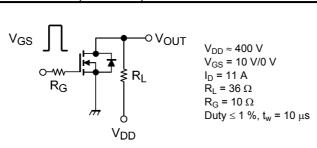


Fig. 6.2.1 Switching Time Test Circuit

#### 6.3. Gate Charge Characteristics ( $T_a = 25$ °C unless otherwise specified)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Total gate charge (gate-source plus gate-drain)	Qg	$V_{DD} \approx 400 \text{ V}, \text{ V}_{GS}$ = 10 V, I <sub>D</sub> = 22 A		50	_	nC
Gate-source charge 1	Q <sub>gs1</sub>		_	14	_	
Gate-drain charge	Q <sub>gd</sub>		_	17	_	

#### 6.4. Source-Drain Characteristics (Ta = 25 °C unless otherwise specified)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Diode forward voltage	V <sub>DSF</sub>	I <sub>DR</sub> = 22 A, V <sub>GS</sub> = 0 V	_	_	-1.7	V
Reverse recovery time	t <sub>rr</sub>	I <sub>DR</sub> = 11 A, V <sub>GS</sub> = 0 V	_	380	_	ns
Reverse recovery charge	Q <sub>rr</sub>	-dI <sub>DR</sub> /dt = 50 A/μs	_	4.5	_	μC
Peak reverse recovery current	I <sub>rr</sub>		_	21	_	А
Diode dv/dt ruggedness	dv/dt	I <sub>DR</sub> = 11 A, V <sub>GS</sub> = 0 V, V <sub>DD</sub> = 400 V	15			V/ns

### TOSHIBA 7. Marking (Note)

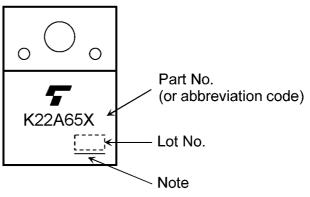
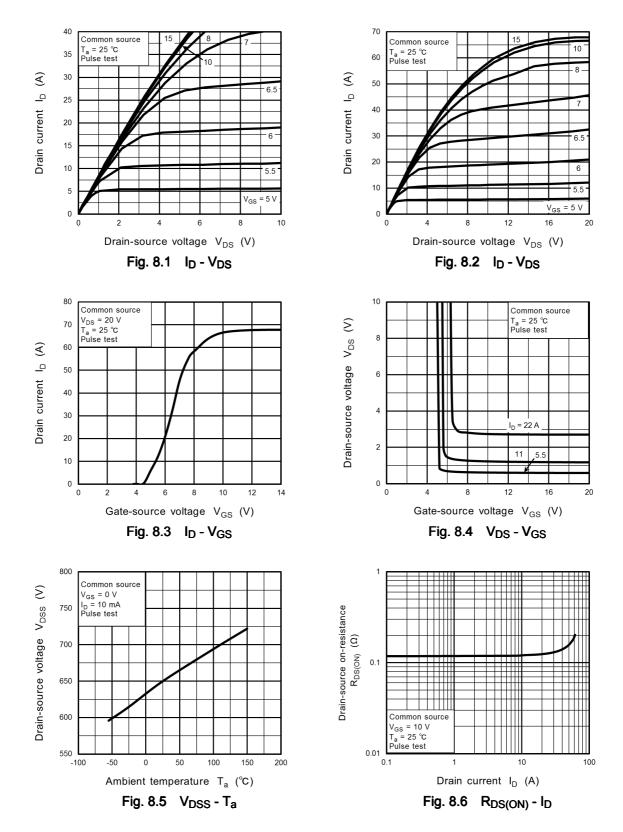


Fig. 7.1 Marking

 Note: A line under a Lot No. identifies the indication of product Labels. Not underlined: [[Pb]]/INCLUDES > MCV Underlined: [[G]]/RoHS COMPATIBLE or [[G]]/RoHS [[Pb]]
Please contact your TOSHIBA sales representative for details as to environmental matters such as the RoHS compatibility of Product.
The RoHS is the Directive 2011/65/EU of the European Parliament and of the Council of 8 June 2011 on the restriction of the use of certain hazardous substances in electrical and electronic equipment.

#### 8. Characteristics Curves (Note)



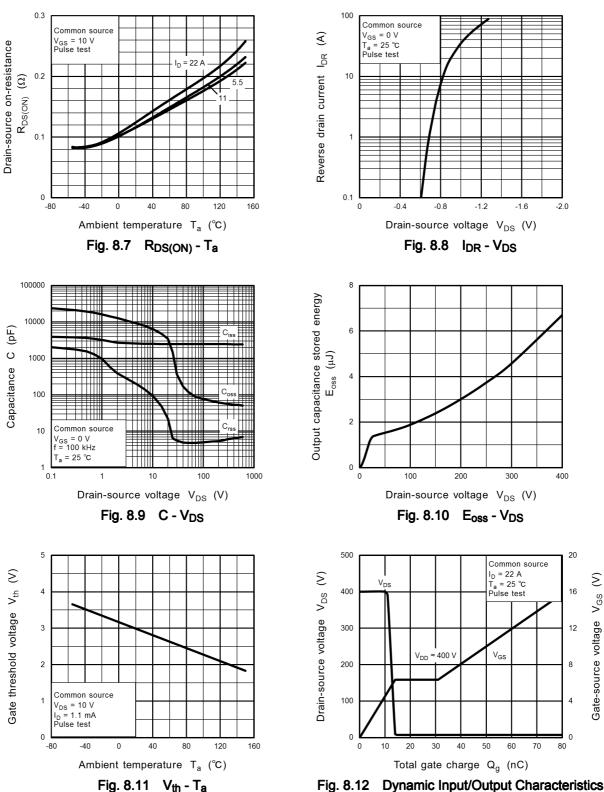
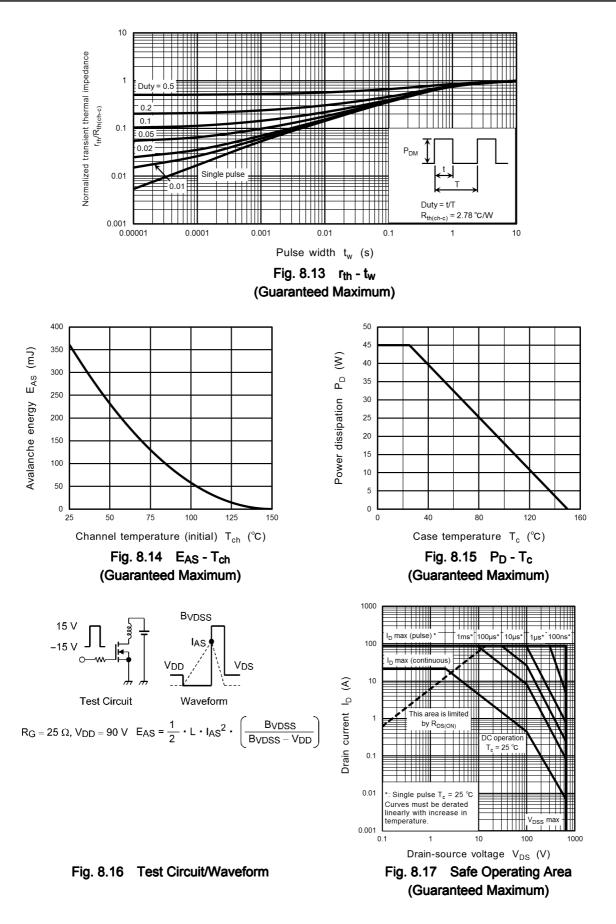


Fig. 8.12 Dynamic Input/Output Characteristics



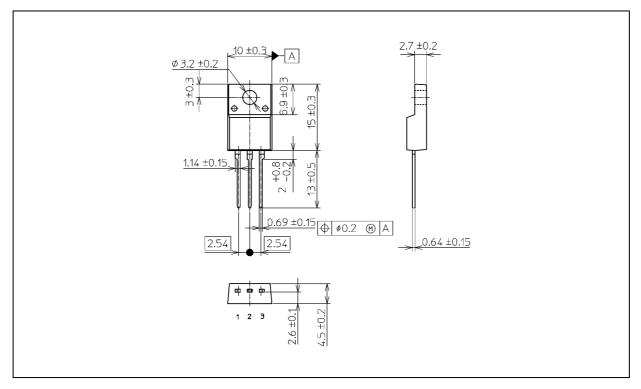
Note: The above characteristics curves are presented for reference only and not guaranteed by production test, unless otherwise noted.



### TK22A65X

#### Package Dimensions

Unit: mm



#### Weight: 1.7 g (typ.)

Package Name(s)	
JEITA: SC-67	
TOSHIBA: 2-10U1S	
Nickname: TO-220SIS	

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